

Notice of References Cited

Application/Control No.

09/776,009

Applicant(s)/Patent Under
Reexamination
VYVODA ET AL.

Examiner

Anh D. Mai

Art Unit

2814

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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.